

# **BUK7608-55A**

# N-channel TrenchMOS standard level FET Rev. 03 — 14 June 2010

**Product data sheet** 

# **Product profile**

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 1.3 Applications

- 12 V and 24 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
l <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	254	W
Static chara	acteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>		-	-	16	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{see } \frac{\text{Figure 12}}{\text{Figure 12}};$		-	6.8	8	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le$ 55 V; $R_{GS}$ = 50 $\Omega$ ; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped	-	-	670	mJ
Dynamic cl	haracteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 0 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 44 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 13	-	35	-	nC

<sup>[1]</sup> Continuous current is limited by package.

# 2. Pinning information

Table 2. Pinning information

	•			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain[1]	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 3	mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7608-55A	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	55	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	<u>[1]</u>	-	-	126	Α
		$T_{mb} = 100  ^{\circ}\text{C};  V_{GS} = 10  \text{V};  \text{see}  \frac{\text{Figure 1}}{}$	[2]	-	-	75	Α
		$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	[2]	-	-	75	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \mu s$ ; pulsed; see Figure 3		-	-	504	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	254	W
T <sub>stg</sub>	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drain	n diode						
Is	source current	T <sub>mb</sub> = 25 °C	[2]	-	-	75	Α
			[1]	-	-	126	Α
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	504	Α
Avalanche ru	uggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup}$ ≤ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	670	mJ

<sup>[1]</sup> Current is limited by power dissipation chip rating.

<sup>[2]</sup> Continuous current is limited by package.

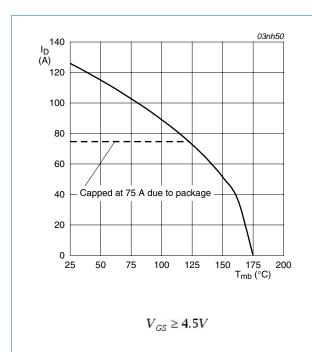
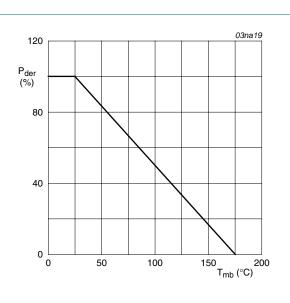
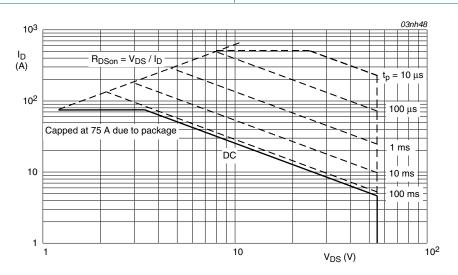


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25$ °C;  $I_{DM}$  is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.59	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed-circuit board; minimum footprint	-	50	-	K/W

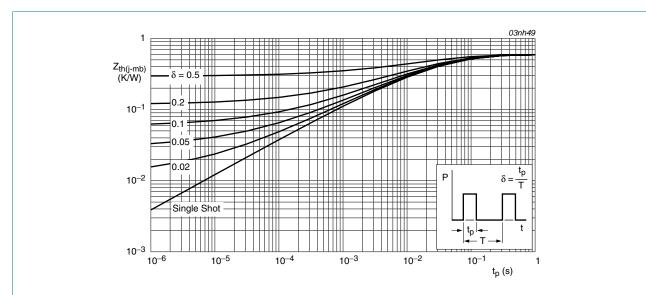


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

# 6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
	voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 175$ °C; see Figure 10	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = 25$ °C; see <u>Figure 10</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 10</u>	-	-	4.4	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
GSS	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{DS} = 0 \text{ V}; V_{GS} = -20 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub> drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	16	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	6.8	8	mΩ
Dynamic (	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 0 \text{ V};$	-	76	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	16	-	nC
$Q_{GD}$	gate-drain charge		-	35	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	3264	4352	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 14</u>	-	719	863	pF
C <sub>rss</sub>	reverse transfer capacitance		-	390	533	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	24	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 \text{ °C}$	-	94	-	ns
d(off)	turn-off delay time		-	100	-	ns
t <sub>f</sub>	fall time		-	80	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25$ °C	-	2.5	-	nΗ
		from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
-s	internal source inductance	from source lead to source bond pad ; $T_j = 25~^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dr	rain diode					
$V_{SD}$	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 15</u>	-	0.85	1.2	V
rr	reverse recovery time	$I_S = 75 \text{ A}$ ; $dI_S/dt = -100 \text{ A/}\mu\text{s}$ ;	-	65	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	170	-	nC

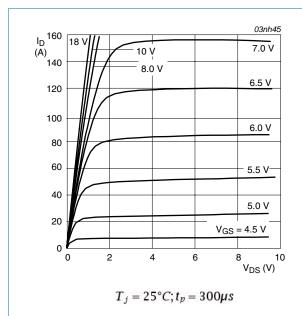


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

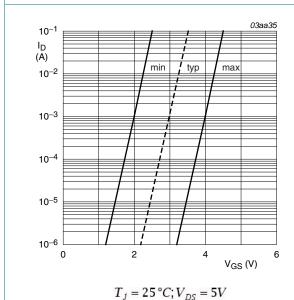


Fig 7. Sub-threshold drain current as a function of gate-source voltage

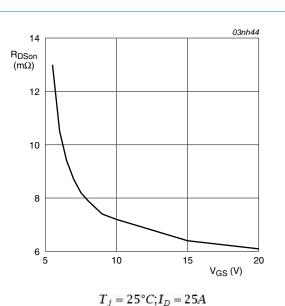


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

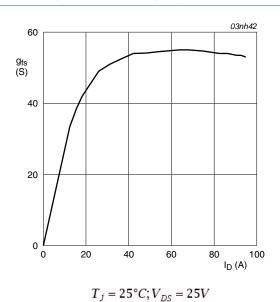


Fig 8. Forward transconductance as a function of drain current; typical values

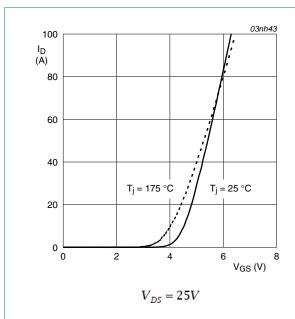


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

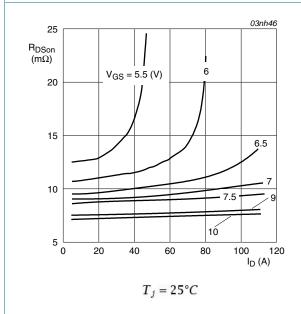
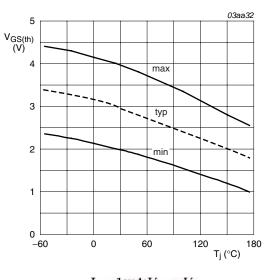


Fig 11. Drain-source on-state resistance as a function of drain current; typical values



 $I_D = 1 mA; V_{DS} = V_{GS}$ 

Fig 10. Gate-source threshold voltage as a function of junction temperature

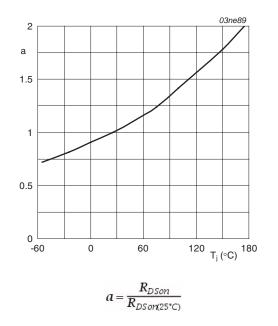


Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature

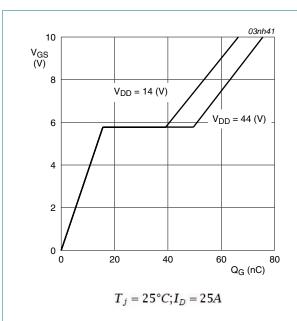


Fig 13. Gate-source voltage as a function of turn-on gate charge; typical values

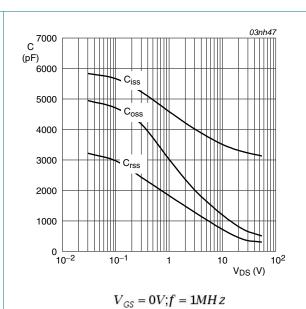


Fig 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

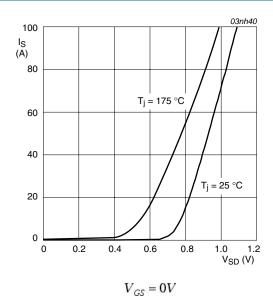


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

# 7. Package outline

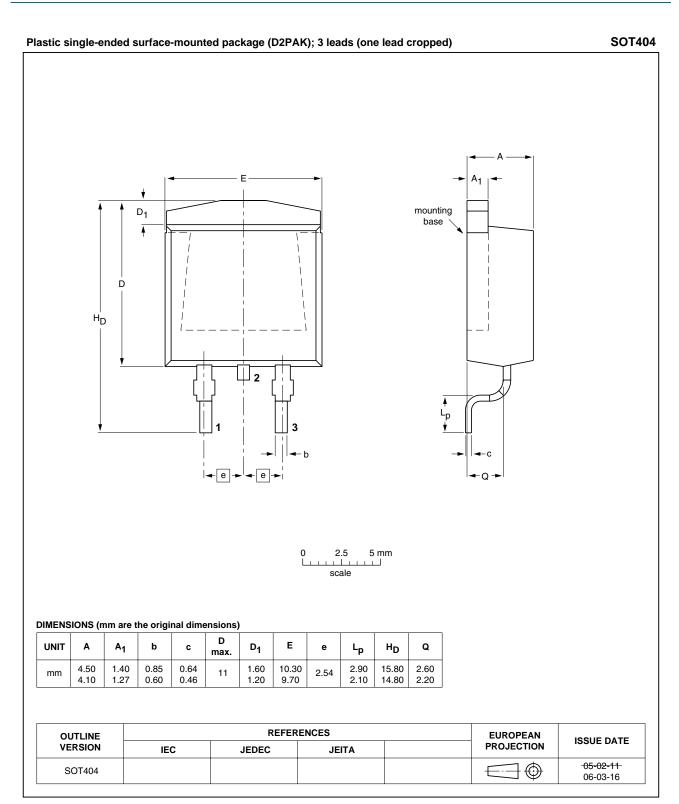


Fig 16. Package outline SOT404 (D2PAK)

# **Revision history**

#### Table 7. **Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7608-55A v.3	20100614	Product data sheet	-	BUK7508_7608_55A v.2
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity guide of NXP Semiconductors.</li> </ul>			
	<ul> <li>Legal texts</li> </ul>	have been adapted to the	new company name where	appropriate.
	<ul> <li>Type number</li> </ul>	er BUK7608-55A separated	d from data sheet BUK7508	3_7608_55A v.2.
BUK7508_7608_55A v.2	20020117	Product specification	-	-

## 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nexperia.com">http://www.nexperia.com</a>.

#### 9.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. Nexperia does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local Nexperia sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between Nexperia and its customer, unless Nexperia and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the Nexperia product is deemed to offer functions and qualities beyond those described in the Product data sheet.

#### 9.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, Nexperia does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall Nexperia be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, Nexperia's aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of Nexperia.

Right to make changes — Nexperia reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This Nexperia product has been qualified for use in automotive applications. The product is not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of a Nexperia product can reasonably be expected to result in personal injury, death or severe property or environmental damage. Nexperia accepts no liability for inclusion and/or use of Nexperia products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. Nexperia makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Nexperia does not accept any liability related to any default, damage, costs or problem which is based on a weakness or default in the customer application/use or the application/use of customer's third party customer(s) (hereinafter both referred to as "Application"). It is customer's sole responsibility to check whether the Nexperia product is suitable and fit for the Application planned. Customer has to do all necessary testing for the Application in order to avoid a default of the Application and the product. Nexperia does not accept any liability in this respect.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding. Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

#### Terms and conditions of commercial sale — Nexperia

products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nexperia.com/profile/terms">http://www.nexperia.com/profile/terms</a>, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. Nexperia hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of Nexperia products by customer.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

BUK7608-55A

All information provided in this document is subject to legal disclaimers.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

## 10. Contact information

For more information, please visit: <a href="http://www.nexperia.com">http://www.nexperia.com</a>

For sales office addresses, please send an email to: <a href="mailto:salesaddresses@nexperia.com">salesaddresses@nexperia.com</a>

# BUK7608-55A

# **Nexperia**

N-channel TrenchMOS standard level FET

# 11. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information
3	Ordering information
4	Limiting values3
5	Thermal characteristics5
6	Characteristics6
7	Package outline10
8	Revision history11
9	Legal information12
9.1	Data sheet status
9.2	Definitions12
9.3	Disclaimers
9.4	Trademarks13
40	Contact information 49

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below:

614233C 648584F IRFD120 JANTX2N5237 2N7000 FCA20N60\_F109 FDZ595PZ 2SK2545(Q,T) 405094E 423220D

TPCC8103,L1Q(CM MIC4420CM-TR VN1206L 614234A 715780A NTNS3166NZT5G SSM6J414TU,LF(T 751625C

IPS70R2K0CEAKMA1 BUK954R8-60E DMN3404LQ-7 NTE6400 SQJ402EP-T1-GE3 2SK2614(TE16L1,Q) 2N7002KW-FAI

DMN1017UCP3-7 EFC2J004NUZTDG ECH8691-TL-W FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7 NTE221 NTE2384

NTE2903 NTE2941 NTE2945 NTE2946 NTE2960 NTE2967 NTE2969 NTE2976 NTE455 NTE6400A NTE2910 NTE2916 NTE2956

NTE2911 US6M2GTR TK10A80W,S4X(S SSM6P69NU,LF